

**METHOD FOR FORMING QUADRUPLE DENSITY SIDEWALL IMAGE
TRANSFER (SIT) STRUCTURES**

Abstract of the Disclosure

5 A method is provided for forming a quadruple density sidewall image
transfer (SIT) structure. Oxide spacers are formed on opposite sidewalls of
a first mandrel. The oxide spacers form a second mandrel. Then sidewall
spacers are formed on opposite sidewalls of the oxide spacers forming the
second mandrel. A pattern of the sidewall spacers is used to form the
quadruple density sidewall image transfer (SIT) structure. The method of
10 the invention enables formation of four well-controlled lines for each
lithographically minimum pitch dimension.